

ABSTRACT

There is provided a novel Ag alloy bonding wire for semiconductor devices which provides an excellent bonded
5 ball shape during ball bonding, which is required for high-density packaging. The Ag alloy bonding wire for semiconductor devices is made of an Ag alloy that contains one or more elements selected from the group consisting of Te, Bi and Sb and that satisfies at least one of the
10 following conditions (1) to (3):
 (1) a concentration of Te is 5 to 500 at. ppm;
 (2) a concentration of Bi is 5 to 500 at. ppm; and
 (3) a concentration of Sb is 5 to 1,500 at. ppm.

15 [No figure]